

What is claimed is:

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1. A method of forming a seal pattern of a liquid crystal display panel having a liquid crystal layer comprising the steps of:
- forming a common electrode over a first substrate;
 - forming a plurality of conductive contact dots on a second substrate;
 - forming a seal pattern along edges of the second substrate, said seal pattern having a plurality of triangular bent portions, the triangular bent portions being bent toward an inside of the second substrate; and
 - forming a liquid crystal layer between the first and second substrates.
2. The method according to claim 1, wherein the conductive contact dot comprises a silver (Ag).
3. The method according to claim 1, wherein the seal pattern of the bent portions include a first, a second, and a third vertexes.
4. The method according to claim 3, wherein the seal pattern has a round with a radius in each of the vertexes.
5. The method according to claim 4, wherein the radius of the first, the second, and the third vertex is 0.5 to 2 millimeters.
6. The method according to claim 4, wherein a distance between the first and

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the second vertexes is 5 to 20 millimeters.

7. The method according to claim 4, wherein a distance between the conductive contact dot and the third vertex of the triangular bent portion is 0.1 to 5 millimeters.

8. The method according to claim 1, wherein the seal pattern forms by a dispenser.

9. A method of forming a seal pattern of a liquid crystal display panel comprising the steps of:

forming a common electrode on a first substrate;

forming a plurality of conductive contact dots on the second substrate;

forming a seal pattern along edges of the second substrate, said seal pattern having a plurality of semicircular bent portions, the semicircular bent portions being bent toward an inside of the second substrate; and

forming a liquid crystal layer between first and second substrates.

10. The method according to claim 9, wherein each of the two ends of the semicircular portion has a radius of 0.5 to 2 mm.

11. The method according to claim 9, wherein a distance between the two ends of the semicircular portion is 5 to 20 millimeters.

12. The method according to claim 9, wherein a distance between the

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conductive contact dot and the semicircular portion is 0.1 to 5 millimeters.